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**Comparative Study on Intersubband Absorption in AlGa<sub>N</sub>/Ga<sub>N</sub> and AlInN/GaN Heterostructures Grown on Low-Defect Substrates**  
COLIN EDMUNDS, LIANG TANG, JIAYI SHAO, DONGHUI LI, GEOFF GARDNER, MICHAEL MANFRA, OANA MALIS, Purdue University, ANDREW GRIER, ZORAN IKONIC, PAUL HARRISON, University of Leeds, DIMITRI ZAKHAROV, Brookhaven National Laboratory — Intersubband (ISB) devices utilizing III-nitrides have attracted attention for near- and far-infrared optoelectronic applications. However, the lattice mismatch between GaN and commonly used substrates results in a high defect density that hinders the vertical transport required for these devices. Furthermore, most devices in the literature utilize AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures for which there is no lattice-matched alloy composition. Due to this lattice mismatch, AlGa<sub>N</sub> is not ideal for the development of complex devices such as quantum cascade lasers that often require active-region thicknesses on the order of microns for efficient operation. Fortunately, exact lattice matching occurs in AlInN/GaN heterostructures at roughly 18% In composition. To investigate the challenges of lattice-matched nitrides, we presents a comparative study of ISB absorption in high-quality AlGa<sub>N</sub>/Ga<sub>N</sub> and near lattice-matched AlInN/GaN heterostructures grown by molecular-beam epitaxy on low-defect free-standing GaN substrates. Experimental measurements of transition energy, integrated absorbance and linewidth were compared to theoretical predictions that included many-body effects, interface roughness and calculations of the transition lifetime.

Colin Edmunds  
Purdue University

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